MC14511B

BCD-To-Seven Segment Latch/Decoder/Driver

The MC14511B BCD–to–seven segment latch/decoder/driver is constructed with complementary MOS (CMOS) enhancement mode devices and NPN bipolar output drivers in a single monolithic structure. The circuit provides the functions of a 4–bit storage latch, an 8421 BCD–to–seven segment decoder, and an output drive capability. Lamp test ($\overline{LT}$), blanking ($\overline{BI}$), and latch enable (LE) inputs are used to test the display, to turn–off or pulse modulate the brightness of the display, and to store a BCD code, respectively. It can be used with seven–segment light–emitting diodes (LED), incandescent, fluorescent, gas discharge, or liquid crystal readouts either directly or indirectly.

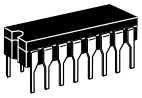
Applications include instrument (e.g., counter, DVM, etc.) display driver, computer/calculator display driver, cockpit display driver, and various clock, watch, and timer uses.

- Low Logic Circuit Power Dissipation
- High–Current Sourcing Outputs (Up to 25 mA)
- Latch Storage of Code
- Blanking Input
- Lamp Test Provision
- Readout Blanking on all Illegal Input Combinations
- Lamp Intensity Modulation Capability
- Time Share (Multiplexing) Facility
- Supply Voltage Range = 3.0 V to 18 V
- Capable of Driving Two Low–power TTL Loads, One Low–power Schottky TTL Load or Two HTL Loads Over the Rated Temperature Range
- Chip Complexity: 216 FETs or 54 Equivalent Gates
- Triple Diode Protection on all Inputs

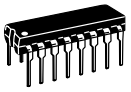
MAXIMUM RATINGS* (Voltages Referenced to V_{SS})

Rating	Symbol	Value	Unit
DC Supply Voltage	V_{DD}	– 0.5 to + 18	V
Input Voltage, All Inputs	V_{in}	– 0.5 to V_{DD} + 0.5	V
DC Current Drain per Input Pin	I	10	mA
Operating Temperature Range	T_A	– 55 to + 125	°C
Power Dissipation per Package†	P_D	500	mW
Storage Temperature Range	T_{stg}	– 65 to + 150	°C
Maximum Output Drive Current (Source) per Output	I_{OHmax}	25	mA
Maximum Continuous Output Power (Source) per Output ‡	P_{OHmax}	50	mW

‡$P_{OHmax} = I_{OH} (V_{DD} - V_{OH})$
* Maximum Ratings are those values beyond which damage to the device may occur.
†Temperature Derating:
Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C
Ceramic “L” Packages: – 12 mW/°C From 100°C To 125°C



L SUFFIX
CERAMIC
CASE 620



P SUFFIX
PLASTIC
CASE 648

D SUFFIX
SOIC
CASE 751B

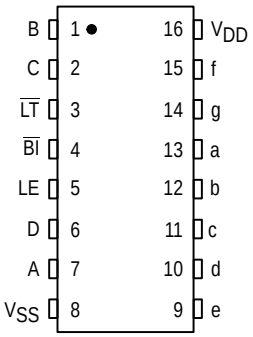
DW SUFFIX
SOIC
CASE 751G

ORDERING INFORMATION

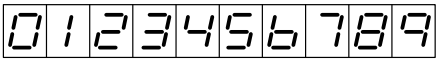
MC14XXXBCP	Plastic
MC14XXXBCL	Ceramic
MC14XXXBDW	SOIC
MC14XXXBD	SOIC

T_A = – 55° to 125°C for all packages.

PIN ASSIGNMENT



DISPLAY



TRUTH TABLE

Inputs							Outputs						
LE	BI	LT	D	C	B	A	a	b	c	d	e	f	g	Display
X	X	0	X	X	X	X	1	1	1	1	1	1	1	8
X	0	1	X	X	X	X	0	0	0	0	0	0	0	Blank
0	1	1	0	0	0	0	1	1	1	1	1	1	0	0
0	1	1	0	0	0	1	0	1	1	0	0	0	0	1
0	1	1	0	0	1	0	1	1	1	1	0	0	1	2
0	1	1	0	0	1	1	1	1	1	1	0	0	1	3
0	1	1	0	1	0	0	0	1	1	0	0	1	1	4
0	1	1	0	1	0	1	1	0	1	1	0	1	1	5
0	1	1	0	1	1	0	0	0	1	1	1	1	1	6
0	1	1	0	1	1	1	1	1	1	0	0	0	0	7
0	1	1	1	0	0	0	1	1	1	1	1	1	1	8
0	1	1	1	0	0	1	1	1	1	0	0	1	1	9
0	1	1	1	0	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	0	1	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	0	0	1	1	1	1	1	1	1	Blank
0	1	1	1	1	0	1	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	0	0	0	0	0	0	0	0	Blank
0	1	1	1	1	1	1	0	0	0	0	0	0	0	Blank
1	1	1	X	X	X	X				*				*

X = Don't Care
* Depends upon the BCD code previously applied when LE = 0

REV 3
1/94

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ #	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level	V_{OL}	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
V_{in} = V_{DD} or 0		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
“1” Level	V_{OH}	5.0	4.1	—	4.1	4.57	—	4.1	—	Vdc
V_{in} = 0 or V_{DD}		10	9.1	—	9.1	9.58	—	9.1	—	
		15	14.1	—	14.1	14.59	—	14.1	—	
Input Voltage # “0” Level	V_{IL}									Vdc
(V_O = 3.8 or 0.5 Vdc)		5.0	—	1.5	—	2.25	1.5	—	1.5	
(V_O = 8.8 or 1.0 Vdc)		10	—	3.0	—	4.50	3.0	—	3.0	
(V_O = 13.8 or 1.5 Vdc)		15	—	4.0	—	6.75	4.0	—	4.0	
“1” Level	V_{IH}									Vdc
(V_O = 0.5 or 3.8 Vdc)		5.0	3.5	—	3.5	2.75	—	3.5	—	
(V_O = 1.0 or 8.8 Vdc)		10	7.0	—	7.0	5.50	—	7.0	—	
(V_O = 1.5 or 13.8 Vdc)		15	11	—	11	8.25	—	11	—	
Output Drive Voltage	V_{OH}									Vdc
(I_{OH} = 0 mA) Source		5.0	4.1	—	4.1	4.57	—	4.1	—	
(I_{OH} = 5.0 mA)			—	—	—	4.24	—	—	—	
(I_{OH} = 10 mA)			3.9	—	3.9	4.12	—	3.5	—	
(I_{OH} = 15 mA)			—	—	—	3.94	—	—	—	
(I_{OH} = 20 mA)			3.4	—	3.4	3.70	—	3.0	—	
(I_{OH} = 25 mA)			—	—	—	3.54	—	—	—	
(I_{OH} = 0 mA)		10	9.1	—	9.1	9.58	—	9.1	—	Vdc
(I_{OH} = 5.0 mA)			—	—	—	9.26	—	—	—	
(I_{OH} = 10 mA)			9.0	—	9.0	9.17	—	8.6	—	
(I_{OH} = 15 mA)			—	—	—	9.04	—	—	—	
(I_{OH} = 20 mA)			8.6	—	8.6	8.90	—	8.2	—	
(I_{OH} = 25 mA)			—	—	—	8.70	—	—	—	
(I_{OH} = 0 mA)		15	14.1	—	14.1	14.59	—	14.1	—	Vdc
(I_{OH} = 5.0 mA)			—	—	—	14.27	—	—	—	
(I_{OH} = 10 mA)			14	—	14	14.18	—	13.6	—	
(I_{OH} = 15 mA)			—	—	—	14.07	—	—	—	
(I_{OH} = 20 mA)			13.6	—	13.6	13.95	—	13.2	—	
(I_{OH} = 25 mA)			—	—	—	13.70	—	—	—	
Output Drive Current	I_{OL}									mAdc
(V_{OL} = 0.4 V) Sink		5.0	0.64	—	0.51	0.88	—	0.36	—	
(V_{OL} = 0.5 V)		10	1.6	—	1.3	2.25	—	0.9	—	
(V_{OL} = 1.5 V)		15	4.2	—	3.4	8.8	—	2.4	—	
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current	I_{DD}	5.0	—	5.0	—	0.005	5.0	—	150	µAdc
(Per Package) V_{in} = 0 or V_{DD},		10	—	10	—	0.010	10	—	300	
I_{out} = 0 µA		15	—	20	—	0.015	20	—	600	
Total Supply Current**†	I_T	5.0	I_T = (1.9 µA/kHz) f + I_{DD}							µAdc
(Dynamic plus Quiescent,		10	I_T = (3.8 µA/kHz) f + I_{DD}							
Per Package)		15	I_T = (5.7 µA/kHz) f + I_{DD}							
(C_L = 50 pF on all outputs, all buffers switching)										

#Noise immunity specified for worst–case input combination.
Noise Margin for both “1” and “0” level =
1.0 Vdc min @ V_{DD} = 5.0 Vdc
2.0 Vdc min @ V_{DD} = 10 Vdc
2.5 Vdc min @ V_{DD} = 15 Vdc

** The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\ pF) + 3.5 \times 10^{-3} (C_L - 50) V_{DD} f$$

where: I_T is in µA (per package), C_L in pF, V_{DD} in Vdc, and f in kHz is input frequency.

SWITCHING CHARACTERISTICS* (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ	Max	Unit
Output Rise Time	t_{TLH}					ns
t_{TLH} = (0.40 ns/pF) C_L + 20 ns		5.0	—	40	80	
t_{TLH} = (0.25 ns/pF) C_L + 17.5 ns		10	—	30	60	
t_{TLH} = (0.20 ns/pF) C_L + 15 ns		15	—	25	50	
Output Fall Time	t_{THL}					ns
t_{THL} = (1.5 ns/pF) C_L + 50 ns		5.0	—	125	250	
t_{THL} = (0.75 ns/pF) C_L + 37.5 ns		10	—	75	150	
t_{THL} = (0.55 ns/pF) C_L + 37.5 ns		15	—	65	130	
Data Propagation Delay Time	t_{PLH}					ns
t_{PLH} = (0.40 ns/pF) C_L + 620 ns		5.0	—	640	1280	
t_{PLH} = (0.25 ns/pF) C_L + 237.5 ns		10	—	250	500	
t_{PLH} = (0.20 ns/pF) C_L + 165 ns		15	—	175	350	
t_{PHL} = (1.3 ns/pF) C_L + 655 ns	t_{PHL}	5.0	—	720	1440	
t_{PHL} = (0.60 ns/pF) C_L + 260 ns		10	—	290	580	
t_{PHL} = (0.35 ns/pF) C_L + 182.5 ns		15	—	200	400	
$\overline{\text{Blank}}$ Propagation Delay Time	t_{PLH}					ns
t_{PLH} = (0.30 ns/pF) C_L + 585 ns		5.0	—	600	750	
t_{PLH} = (0.25 ns/pF) C_L + 187.5 ns		I0	—	200	300	
t_{PLH} = (0.15 ns/pF) C_L + 142.5 ns		15	—	150	220	
t_{PHL} = (0.85 ns/pF) C_L + 442.5 ns	t_{PHL}	5.0	—	485	970	
t_{PHL} = (0.45 ns/pF) C_L + 177.5 ns		10	—	200	400	
t_{PHL} = (0.35 ns/pF) C_L + 142.5 ns		15	—	160	320	
$\overline{\text{Lamp Test}}$ Propagation Delay Time	t_{PLH}					ns
t_{PLH} = (0.45 ns/pF) C_L + 290.5 ns		5.0	—	313	625	
t_{PLH} = (0.25 ns/pF) C_L + 112.5 ns		10	—	125	250	
t_{PLH} = (0.20 ns/pF) C_L + 80 ns		15	—	90	180	
t_{PHL} = (1.3 ns/pF) C_L + 248 ns	t_{PHL}	5.0	—	313	625	
t_{PHL} = (0.45 ns/pF) C_L + 102.5 ns		10	—	125	250	
t_{PHL} = (0.35 ns/pF) C_L + 72.5 ns		15	—	90	180	
Setup Time	t_{su}	5.0	100	—	—	ns
		10	40	—	—	
		15	30	—	—	
Hold Time	t_h	5.0	60	—	—	ns
		10	40	—	—	
		15	30	—	—	
Latch Enable Pulse Width	t_{WL}	5.0	520	260	—	ns
		10	220	110	—	
		15	130	65	—	

* The formulas given are for the typical characteristics only.

This device contains protection circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit. A destructive high current mode may occur if V_{in} and V_{out} are not constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Due to the sourcing capability of this circuit, damage can occur to the device if V_{DD} is applied, and the outputs are shorted to V_{SS} and are at a logical 1 (See Maximum Ratings).

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}).

Input LE low, and Inputs D, $\overline{BI}$ and $\overline{LT}$ high.
f in respect to a system clock.
All outputs connected to respective C_L loads.

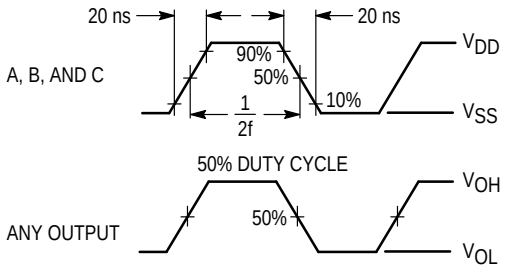
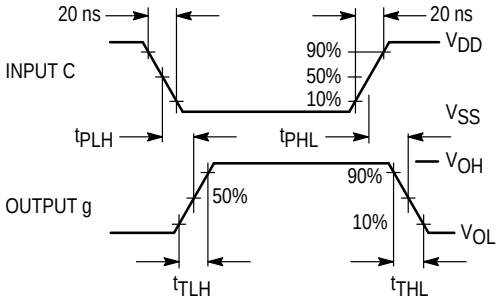
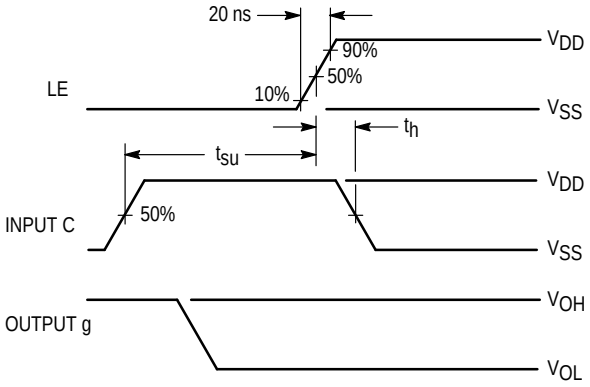


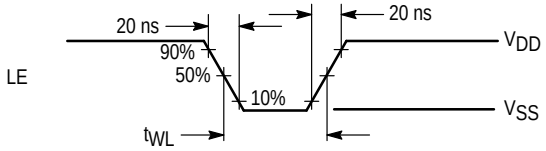
Figure 1. Dynamic Power Dissipation Signal Waveforms



(a) Inputs D and LE low, and Inputs A, B, $\overline{BI}$ and $\overline{LT}$ high.



(b) Input D low, Inputs A, B, $\overline{BI}$ and $\overline{LT}$ high.

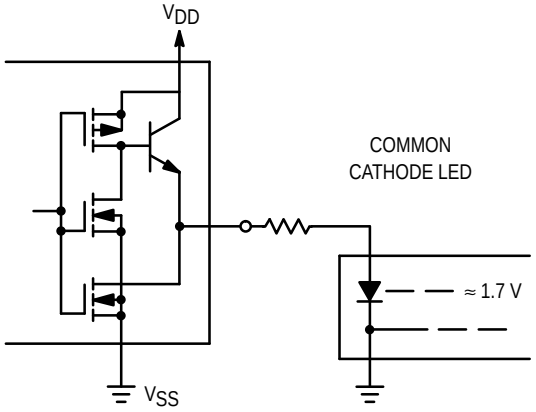


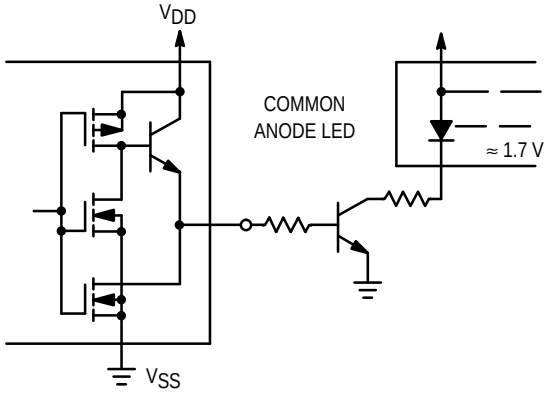
(c) Data DCBA strobed into latches.

Figure 2. Dynamic Signal Waveforms

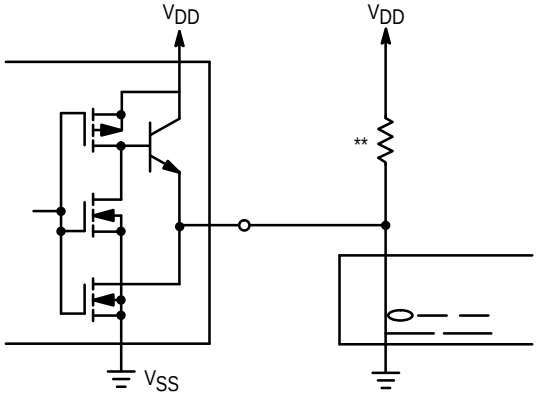
CONNECTIONS TO VARIOUS DISPLAY READOUTS

LIGHT EMITTING DIODE (LED) READOUT

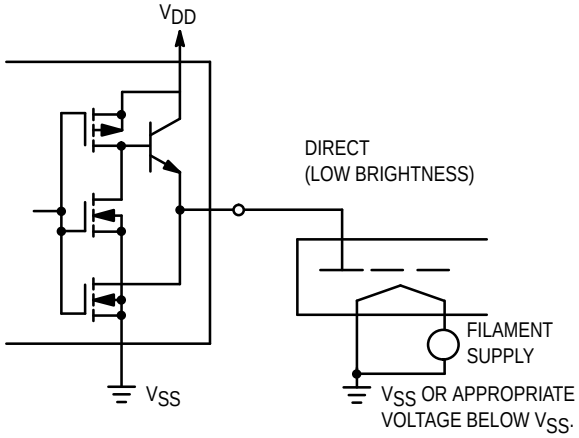




INCANDESCENT READOUT

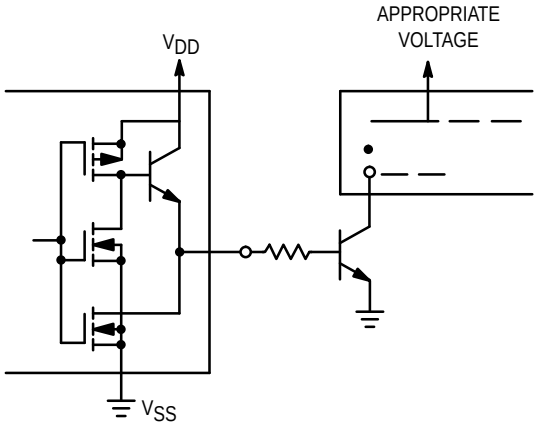


FLUORESCENT READOUT

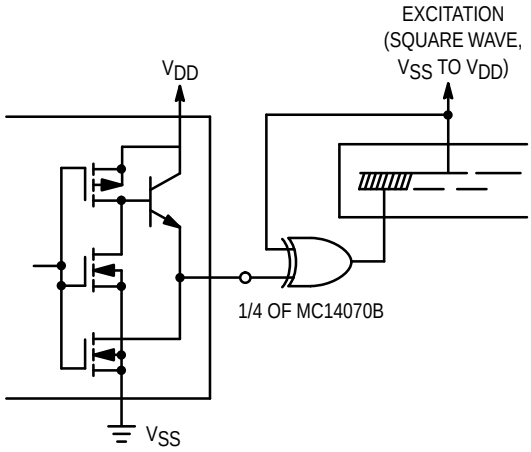


(CAUTION: Maximum working voltage = 18.0 V)

GAS DISCHARGE READOUT



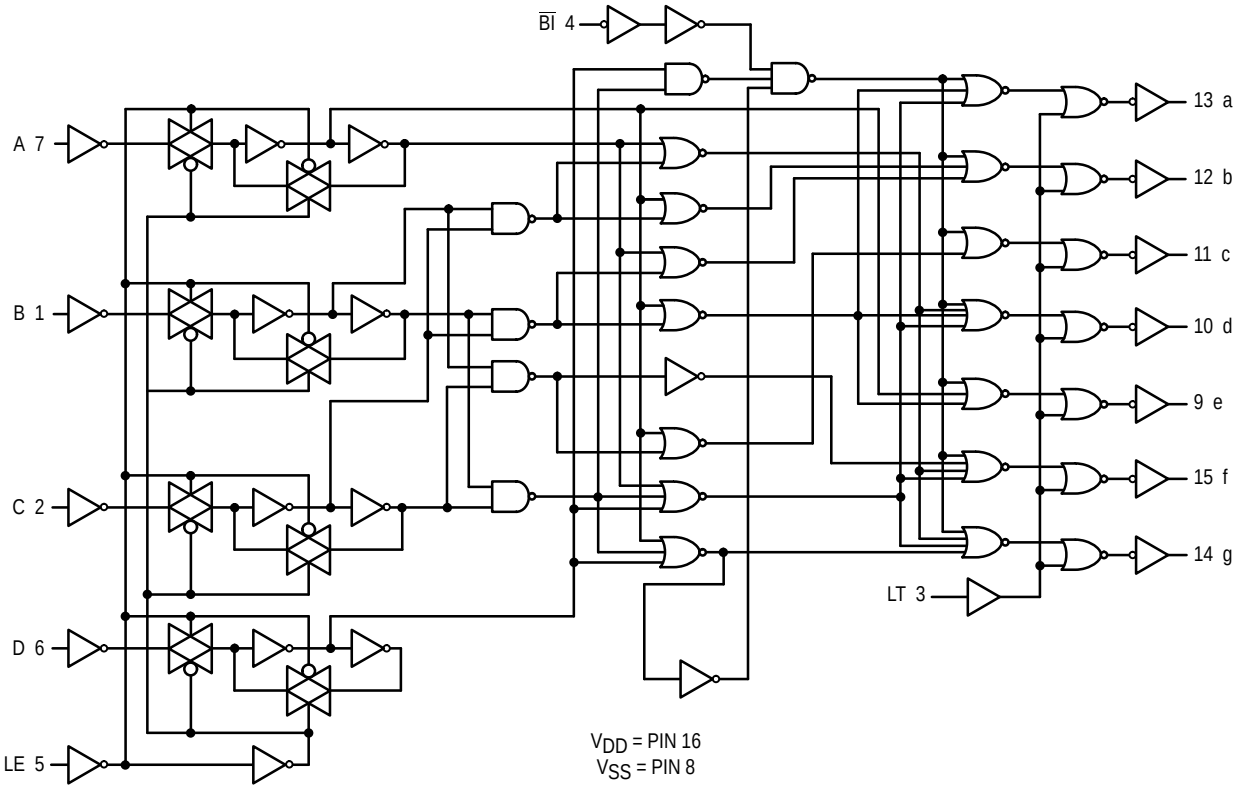
LIQUID CRYSTAL (LCD) READOUT



** A filament pre–warm resistor is recommended to reduce filament thermal shock and increase the effective cold resistance of the filament.

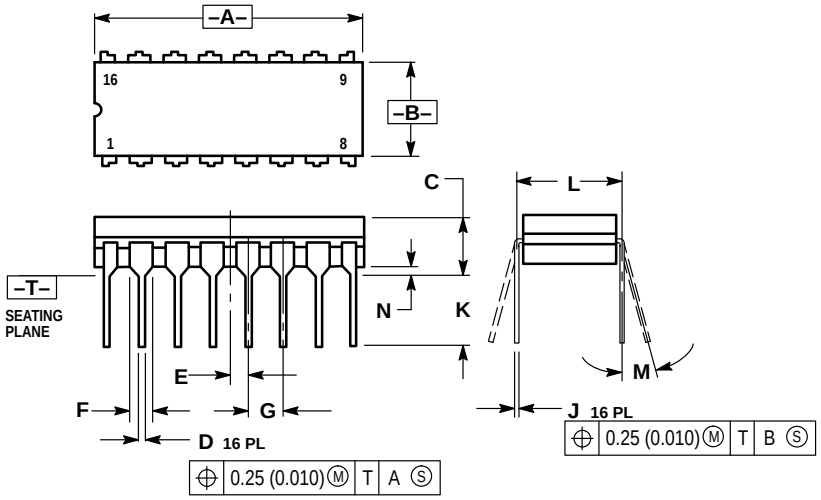
Direct dc drive of LCD's not recommended for life of LCD readouts.

LOGIC DIAGRAM



OUTLINE DIMENSIONS

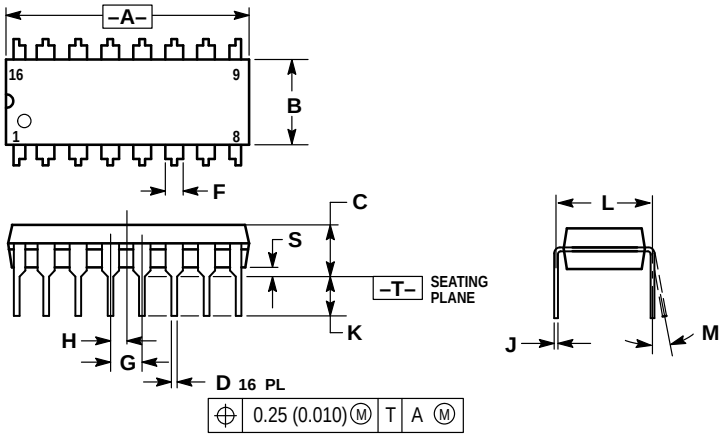
L SUFFIX
CERAMIC DIP PACKAGE
CASE 620–10
ISSUE V



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	—	0.200	—	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
H	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0 °	15 °	0 °	15 °
N	0.020	0.040	0.51	1.01

P SUFFIX
PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R

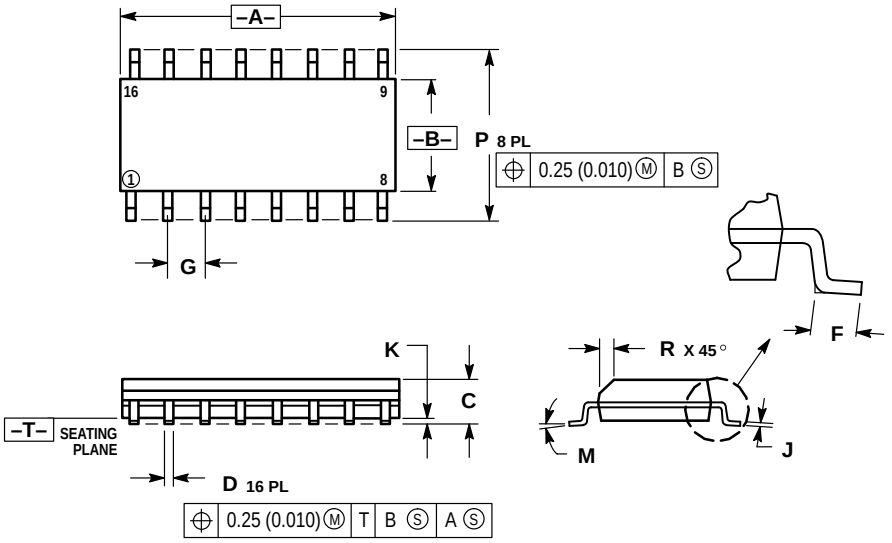


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

OUTLINE DIMENSIONS

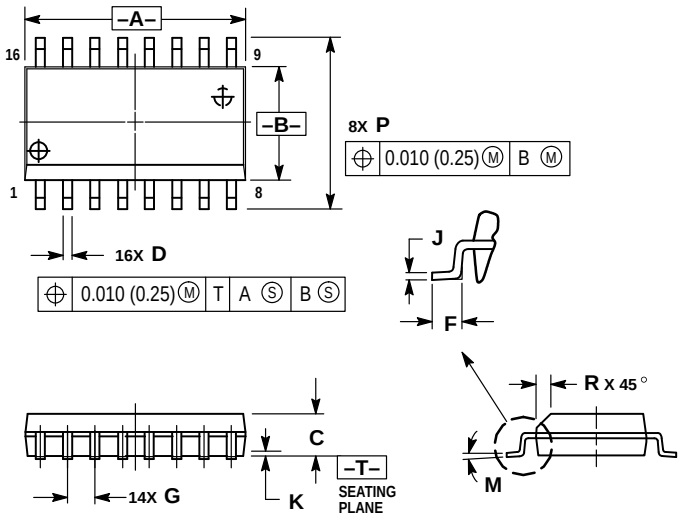
D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

DW SUFFIX
PLASTIC SOIC PACKAGE
CASE 751G–02
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	10.15	10.45	0.400	0.411
B	7.40	7.60	0.292	0.299
C	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.50	0.90	0.020	0.035
G	1.27 BSC		0.050 BSC	
J	0.25	0.32	0.010	0.012
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

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